

2SC4278

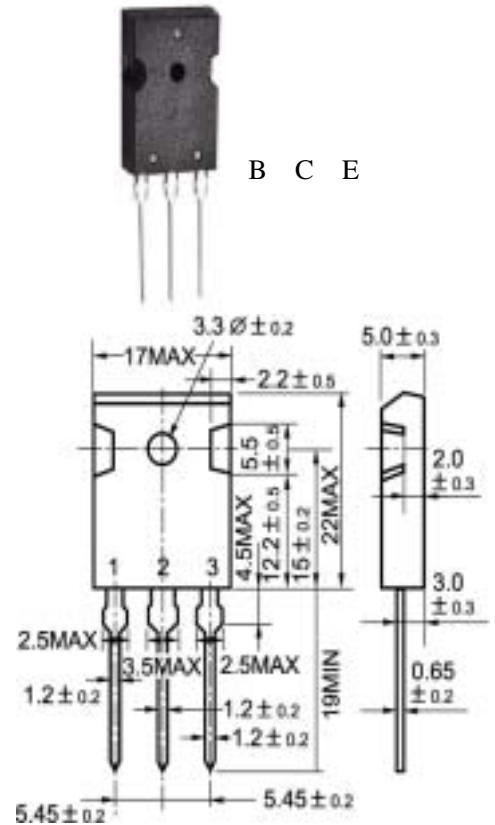
Silicon NPN Transistors

◆ Features

- With TO-247 package
- Complement to type 2SA1633

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	150	V
V _{CEO}	Collector to emitter voltage	150	V
V _{CER}	Emitter to base voltage		
V _{EB}	Emitter to base voltage	5	V
I _B	Base Current		
I _C	Collector current-Continuous	10	A
P _D	Total Power Dissipation@TC=25°C Derate above 25°C	100	W W/°C
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-65~150	°C



TO-247

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C =30mA; I _B =0	150		V
V _{CBO}	Collector-Base Voltage	I _C =1mA; I _E =0	150		V
I _{CEO}	Collector Cutoff Current	V _{CE} =150V; I _B =0		500	uA
I _{CBO}	Collector Cutoff Current	V _{CB} =150V; I _E =0		100	uA
I _{EBO}	Emitter Cutoff Current				
V _{EBO}	Emitter Cutoff Current	I _E =5mA; I _C =0	5		V
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =5A; I _B =0.5A		2.0	V
V _{CE(sat-2)}	Collector-emitter saturation voltages				
V _{CE(sat-3)}	Collector-emitter saturation voltages				
V _{CE(sat-4)}	Collector-emitter saturation voltages				
h _{FE-1}	Forward current transfer ratio	I _C =1A; V _{CE} =5V	60	320	
h _{FE-2}	Forward current transfer ratio				
V _{BE(sat)}	Base-emitter Saturation voltages				
f _T	Current Gain-Bandwidth Product				